

1	<b>MAGNETIC BUBBLES</b>	185.08	..With volatile signal storage device
2	.Disposition of elements	185.09	..Error correction (e.g., redundancy, endurance)
3	..Lattice	185.1	..Extended floating gate
4	.Decoder	185.11	..Bank or block architecture
5	.Logic	185.12	...Parallel row lines (e.g., page mode)
6	.Rotating field circuits	185.13	...Global word or bit lines
7	.Detectors	185.14	..Program gate
8	..Magnetoresistive	185.15	...Weak inversion injection
9	..Hall effect	185.16	..Virtual ground
10	..Optical	185.17	..Logic connection (e.g., NAND string)
11	.Generators	185.18	.Particular biasing
12	..By splitting	185.19	..Multiple pulses (e.g., ramp)
13	.Plural interacting paths	185.2	..Reference signal (e.g., dummy cell)
14	..Closed loop	185.21	...Sensing circuitry (e.g., current mirror)
15	...Major-minor	185.22	...Verify signal
16	..With switch at interacting point	185.23	..Drive circuitry (e.g., word line driver)
17	...Idler switch	185.24	..Threshold setting (e.g., conditioning)
18	..Boundary	185.25	..Line charging (e.g., precharge, discharge, refresh)
19	.Conductor propagation	185.26	..Floating electrode (e.g., source, control gate, drain)
20	..Including A.C. signal	185.27	..Substrate bias
21	..Three phase signals	185.28	..Tunnel programming
22	.One's and zero's	185.29	..Erase
23	.Plural direction propagation	185.3	...Over erasure
24	..Nonsequential	185.31	...Nonsubstrate discharge
25	.Velocity	185.32	...Radiation erasure
26	..Turns	185.33	...Flash
27	.Bias	45	<b>ANALOG STORAGE SYSTEMS</b>
28	..Variable	46	.Resistive
29	.Strip domain	47	.Thermoplastic
30	.In-plane field (nonrotating)	48	.Magnetic
31	.Different size bubbles	49.1	<b>ASSOCIATIVE MEMORIES (CONTENT ADDRESSABLE MEMORY-CAM)</b>
32	.Multiple magnetic layer	49.11	.Flip-Flop
33	.Magnetic storage material	49.12	.Capacitor cell
34	..Amorphous	49.13	.Ferroelectric cell
35	.Guide structure	50	.Magnetic cell
36	..Ion implantation	49.15	.Auxiliary lines
37	..Slots or rails	49.16	.Segmented/partitioned of cells
38	..Zigzag	49.17	.Compare/Search/Match circuit
39	..Overlays	49.18	.Priority encoders
40	...On opposite sides of storage medium	51	<b>FORMAT OR DISPOSITION OF ELEMENTS</b>
41	...Dots	52	<b>HARDWARE FOR STORAGE ELEMENTS</b>
42	...Wedges	53	.Shields
43	...Chevrons		
44	...Rectangular bars		
185.01	<b>FLOATING GATE</b>		
185.02	.Disturbance control		
185.03	.Multiple values (e.g., analog)		
185.04	.Data security		
185.05	.Particular connection		
185.06	..Segregated columns		
185.07	..Cross-coupled cell		

54	.Ground plane	105	..Diodes
55	.Magnetic	106	<b>RADIANT ENERGY</b>
56	..Spacers	107	.Chemical fluids
57	..Keeper	108	.Liquid crystal
58	..Slot	109	.Photoconductive and ferroelectric
59	..Embedded conductor		
60	..Air gap	110	.Electroluminescent and photoconductive
61	..Hairpin conductor	111	.Electroluminescent
62	..Permanent magnet	112	.Photoconductive
63	<b>INTERCONNECTION ARRANGEMENTS</b>	113	.Amorphous
64	.Optical	114	.Semiconductive
65	.Ferroelectric	115	..Diodes
66	.Magnetic	116	.Plasma
67	..Plural diagonal	117	.Ferroelectric
68	..Tree	118	.Electron beam
69	..Crossover	119	.Color centers
70	..Woven	120	<b>INFORMATION MASKING</b>
71	.Negative resistance	121	.Polarization
72	.Transistors or diodes	122	..Magneto-optical
73	<b>RECIRCULATION STORES</b>	123	.Bragg cells
74	.Magnetic	124	.Diffraction
75	.Stepwise	125	..Holograms
76	.Delay lines	126	.Thermoplastic
77	.Plural paths	127	.Transparency
78	<b>PLURAL SHIFT REGISTER MEMORY DEVICES</b>	128	.Electron beams
80	<b>MAGNETIC SHIFT REGISTERS</b>	129	<b>SYSTEMS USING PARTICULAR ELEMENT</b>
81	.Bidirectional	130	.Three-dimensional magnetic array
82	.Two cells per bit	131	.Two magnetic cells per bit
83	.SiPo/PiSo	132	.Different size cores
84	.Core in transfer loop	133	.Cells of diverse coercivity
85	.Continuous	134	.Continuous cells
86	..Plated wire	135	..Elongated or bar-shaped cell
87	.Thin film	136	...Twisters
88	..Domain tip	137	...Tubular
89	.Logic	138	...Chain
90	.Multiaperture cell	139	...Plated wire
91	..Ladder	140	.Multiaperture cell
92	..With other type core	141	..Aperture plate
93	.Including delay means	142	..Aperture with transverse axis
94	<b>READ ONLY SYSTEMS (I.E., SEMIPERMANENT)</b>	143	...Biax
95	.With override (i.e., latent images)	144	..Same size apertures
96	.Fusible	145	.Ferroelectric
97	.Magnetic	146	.Electrets
98	..Random core	147	.Persistent internal polarization (PIP)
99	..Random wiring	148	.Resistive
100	.Resistive	149	.Capacitors
101	.Inductive	150	..Inherent
102	.Capacitative	151	.Molecular or atomic
103	.Semiconductive	152	..Nuclear induction or spin echo
104	..Transistors	153	.Electrochemical
		154	.Flip-flop (electrical)

155	..Plural emitter or collector	189.09	.Including reference or bias voltage generator
156	..Complementary		
157	.Magnetostrictive or piezoelectric	189.11	.Including level shift or pull-up circuit
158	.Magnetoresistive	189.12	.With shift register
159	.Negative resistance	190	.For complementary information
160	.Superconductive	191	.Signals
161	..Thin film	192	..Radio frequency
162	..Josephson	193	..Strobe
163	.Amorphous (electrical)	194	..Delay
164	.Electrical contacts	195	..Inhibit
165	..Coherer	196	...Sense/inhibit
166	..Relay	197	..Microwave
167	.Simulating biological cells	198	..Transmission
168	.Ternary	199	..Coincident A.C. signal with pulse
169	.Gunn effect		
170	.Hall effect	200	.Bad bit
171	.Magnetic thin film	201	.Testing
172	..Isotropic	202	.Complementing/balancing
173	..Multiple magnetic storage layers	203	.Precharge
174	.Semiconductive	204	.Accelerating charge or discharge
175	..Diodes	205	.Flip-flop used for sensing
176	..Silicon on sapphire (SOS)	206	.Noise suppression
177	..Bioplar and FET	207	.Differential sensing
178	..Ion implantation	208	..Semiconductors
179	..Plural emitter or collector	209	..Magnetic
180	..Four layer devices	210.1	..Reference or dummy element
181	..Complementary conductivity	210.11	...Compensate signal
182	..Insulated gate devices	210.12	...Voltage setting
183	...Charge coupled	210.13	...Common bit line
184	...Variable threshold	210.14	...Plural elements per reference cell
186	..Single device per bit	210.15	...Structural component of a reference cell
187	..Three devices per bit		
188	..Four or more devices per bit	211	..Temperature compensation
189.011	<b>READ/WRITE CIRCUIT</b>	212	...Semiconductor
189.02	.Multiplexing	213	...Magnetic
189.03	.Plural use of terminal	214	..Particular wiring
189.04	.Simultaneous operations (e.g., read/write)	215	.Optical
189.14	.Common read and write circuit	216	..Holographic
189.15	.Particular read circuit	217	.Electron beam
189.16	.Particular write circuit	218	.Erase
189.17	.Data transfer circuit	219	.SiPo/PiSo
189.18	.Bidirectional bus	220	.Parallel read/write
189.19	.Separate read and write bus	221	.Serial read/write
189.2	.Using different memory types	222	.Data refresh
189.05	.Having particular data buffer or latch	223	.Bridge
189.06	.Including signal clamping	224	.Eddy current
189.07	.Including signal comparison	225	.Minor loop
189.08	.Including specified plural element logic arrangement	225.5	.Including magnetic element
		225.6	.Having bipolar circuit element
		225.7	.Having fuse element
		226	<b>POWERING</b>
		227	.Conservation of power

- 228 .Data preservation  
 229 ..Standby power  
 230.01 **ADDRESSING**  
 230.02 .Multiplexing  
 230.03 .Plural blocks or banks  
 230.04 ..Alternate addressing (e.g., even/odd)  
 230.05 .Multiple port access  
 230.06 .Particular decoder or driver circuit  
 230.07 ..Including magnetic element  
 230.08 .Including particular address buffer or latch circuit arrangement  
 230.09 .Combined random and sequential addressing  
 231 .Using selective matrix  
 232 ..Magnetic  
 233.1 .Sync/clocking  
 233.11 ..Plural clock signals  
 233.12 ..External clock signal modification  
 233.13 ..DDR (double data rate) memory  
 233.14 ..Initiating signal  
 233.15 ..Standby signal  
 233.16 ..Write mode signal only  
 233.17 ..Read mode signal only  
 233.18 ..Burst mode signal  
 233.19 ..Common read and write mode signal  
 233.5 ..Transition detection  
 234 .Optical  
 235 ..Page memories  
 236 .Counting  
 237 .Electron beam  
 238 .Cartesian memories  
 238.5 .Byte or page addressing  
 239 .Sequential  
 240 ..Using shift register  
 241 ..Detectors  
 242 .Current steering  
 243 ..Diode  
 243.5 .Including magnetic element  
 244 **MISCELLANEOUS**
- Any foreign patents or nonpatent literature from subclasses that have been reclassified have been transferred directly to FOR Collection listed below. These Collections contain ONLY foreign patents or nonpatent literature. Parenthetical references in the Collection titles refer to the abolished subclasses from which these Collections were derived.
- FOR 100 **ASSOCIATIVE MEMORIES (365/49)**  
 FOR 101 **READ/WRITE CIRCUIT (365/189.01)**  
 .Noise suppression (365/206)  
 ..Differential sensing (365/207)  
 ...Semiconductor (365/208)  
 ...Magnetic (365/209)  
 FOR 102 ...Reference or dummy elements (365/210)  
**ADDRESSING (365/230.01)**  
 FOR 103 .Sync/clocking (365/233)

**FOREIGN ART COLLECTIONS**FOR 000 **CLASS-RELATED FOREIGN DOCUMENTS**